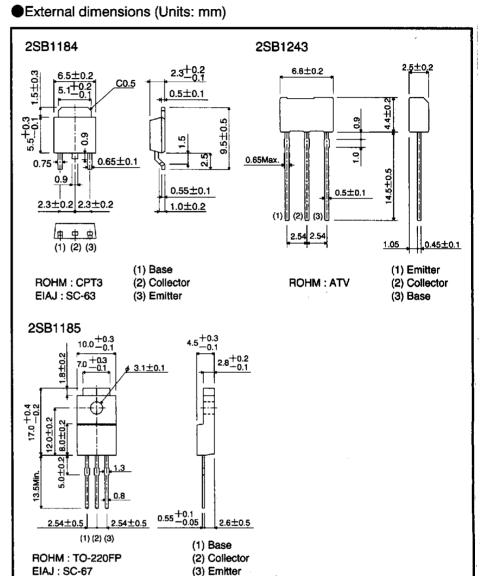
Bi-polar transistors

Power Transistor (-60V, -3A) 2SB1184/2SB1243/2SB1185

Features

- 1) Low $V_{CE(sat)}$. $V_{CE(sat)} = -0.5V$ (Typ.) ($I_{C}/I_{B} = -2A/-0.2A$)
- Complements the 2SD1760/ 2SD1864/2SD1762.
- Structure
 Epitaxial planar type
 PNP silicon transistor



●Absolute maximum ratings (Ta = 25℃)

| Parameter | | Symbol | Limits | Unit | |
|--------------------------------|---------|--------|------------|--------------|--|
| Collector-base voltage | | Vсво | -60 | ٧ | |
| Collector-emitter voltage | | VCEO | -50 | V | |
| Emitter-base voltage | | VEBO | - 5 | V | |
| • | | lc | -3 | A (DC) | |
| Collector curren | τ | lcp | -4.5 | A (Pulse) *1 | |
| | 2SB1184 | 3 Pc | 1 | W | |
| Callagter name | | | 15 | W(Tc=25℃) | |
| Collector power dissipation | 2SB1243 | | Pc 1 | w *2 | |
| dissipation | 2SB1185 | | 2 |] ** | |
| | | | 25 | W(Tc=25℃) | |
| Junction temperature | | Tj | 150 | c | |
| Storage temperature | | Tstg | -55~150 | Ĉ | |

^{*1} Single pulse Pw=100ms

●Electrical characteristics (Ta = 25°C)

| Parameter | | Symbol | Min. | Тур. | Max. | Unit | Conditions | |
|--------------------------------------|------------------|----------|------------|------|------------|------|---|--|
| Collector-base breakdown voltage | | ВУсво | -60 | _ | _ | ٧ | Ic=-50 μA | |
| Collector-emitter breakdown voltage | | BVceo | -50 | | | ٧ | Ic=-1mA | |
| Emitter-base breakdown voltage | | BVEBO | — 5 | _ | | ٧ | I _E =-50 μA | |
| Collector cutoff current | | Ісво | | | — 1 | μΑ | V _{CB} =-40V | |
| Emitter cutoff current | | lebo | _ | _ | -1 | μΑ | V _{EB} =-4V | |
| Collector-emitter saturation voltage | | VCE(sat) | _ | | -1 | ٧ | Ic/I _B =-2A/-0.2A * | |
| Base-emitter saturation voltage | | VBE(sat) | _ | _ | -1.5 | ٧ | Ic/I _B =-2A/-0.2A * | |
| DC current | 2SB1184, 2SB1243 | hfe | 82 | _ | 390 | _ | Vc==-3V lc=-0.5A * | |
| transfer ratio | 2SB1185 | HE | 60 | _ | 320 | _ | VcE=-3V, Ic=-0.5A * | |
| Transition frequency | | f⊤ | | 70 | _ | MHz | V _{CE} =-5V, I _E =0.5A, f=30MHz | |
| Output capacitance | | Cob | _ | 50 | | pF | VcB=-10V, IE=0A, f=1MHz | |

^{*} Measured using pulse current.

●Packaging specifications and hFE

| | | Package | Tap | Bulk | |
|---------|-----|------------------------------|------|------|-----|
| | | Code | TL | TV2 | _ |
| Туре | hfE | Basic ordering unit (pieces) | 2500 | 2500 | 200 |
| 2SB1184 | PQR | | 0 | _ | |
| 2SB1243 | PQR | | _ | 0 | _ |
| 2SB1185 | DEF | | _ | _ | 0 |

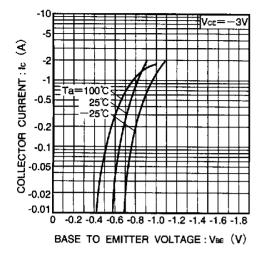
hre values are classified as follows:

| Item | D | E | F |
|------|--------|---------|---------|
| hFE | 60~120 | 100~200 | 160~320 |

| Item | Р | Q | R |
|------|--------|---------|---------|
| hfe | 82~180 | 120~270 | 180~390 |

^{*2} Printed circuit board 1.7mm thick, collector copper plating 1cm² or larger.

Electrical characteristic curves



Grounded emitter propagation characteristics

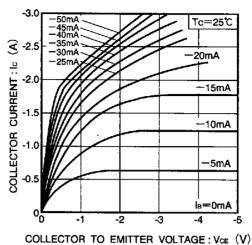
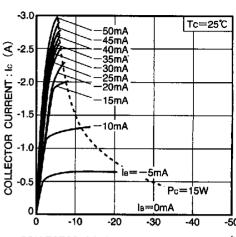
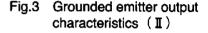


Fig.2 Grounded emitter output



COLLECTOR TO EMITTER VOLTAGE: Voe (V)

characteristics (I)



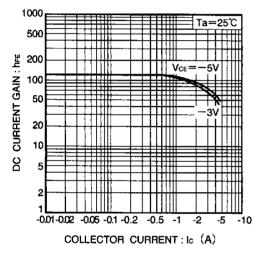


Fig.4 DC current gain vs. collector current (I)

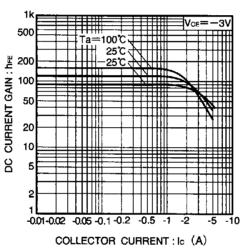
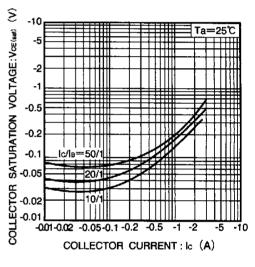
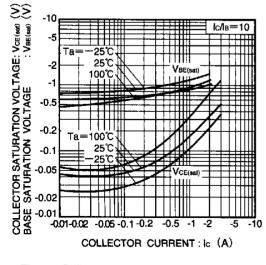


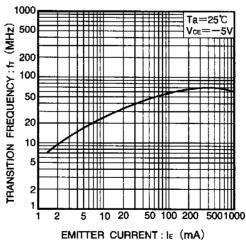
Fig.5 DC current gain vs. collector current (II)



Collector-emitter saturation Fig.6 voltage vs.collector current



Collector-emitter saturation voltage vs. collector current Base-emitter saturation voltage vs. collector current



Gain bandwidth product vs. emitter current

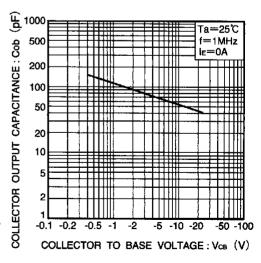


Fig.9 Collector output capacitance vs. collector base voltage

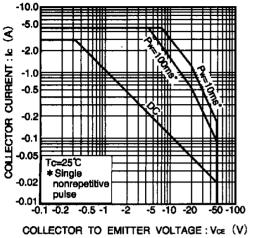


Fig.10 Safe operation area (2SB1184)

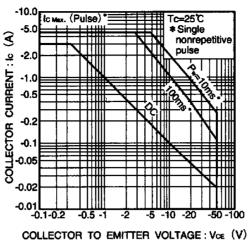


Fig.11 Safe operation area (2SB1243)

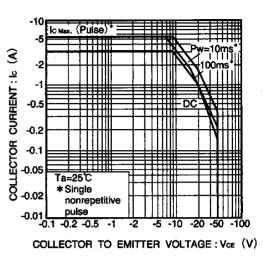


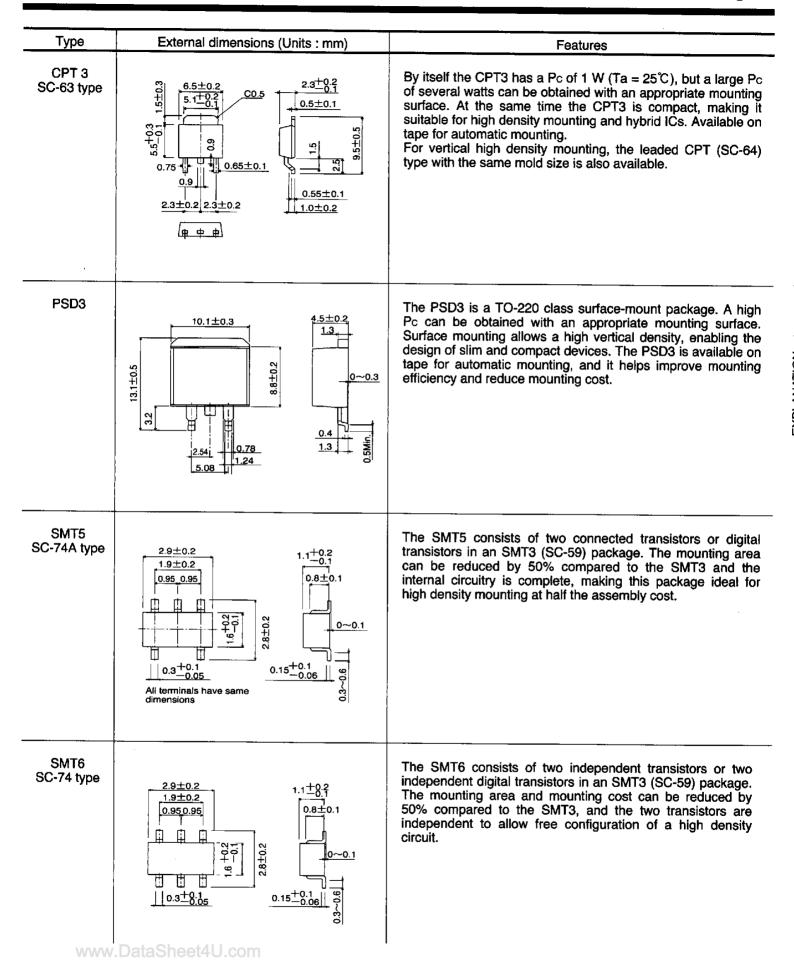
Fig.12 Safe operation area (2SB1185)

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

Types and features of surface-mount packages

| Туре | External dimensions (Units : mm) | Features |
|---------------------|---|---|
| EMT3 SC-75A type | 0.2+0.1 0.2+0.1 0.2+0.1 0.2+0.1 0.2+0.1 0.1±0.55 0.1±0.55 0.3+0.1 0.3+0.1 0.3+0.1 0.15±0.05 | A more compact version of the UMT3 (SC-70), the EMT3 is the world's smallest transistor with a mold size of 1.6 × 0.8 mm. The mounting area is approximately 60% of the UMT3 and 30% of the SMT3, making it ideal for ultra-high density mounting. Mounting is possible with the same type of automatic mounting machine as the UMT3. |
| UMT3 SC-70 type | 2.0±0.2 1,3±0.1 0,65 0.65 0.2 0.7±0.1 0.3+0.1 0.15±0.05 All terminals have same dimensions | The UMT3 is a smaller version of the SMT3 (SC-59). The mounting area is approximately 60% of the SMT3, making it optimum for high density mounting. The taping size is the same as the SMT3, allowing use of conventional automatic mounting machines. Electrical characteristics and reliability are the same as the SMT3. |
| SMT3 SC-59 type | 2.9±0.2 1.1±0.2 0.950.95 0.8±0.1 0~0.1 All terminals have same dimensions 0.4+0.1 0.15-0.06 0.15-0.06 | The SMT3 is a compact package suitable for small electronic devices and hybrid IC applications. With proven performance, this is one of the most basic small packages. With the exception of Pc (collector power dissipation), electrical characteristics are similar to leaded packages. Reliability is on the same level as the TO-92. |
| MPT3 SC-62 type | 4.5 ^{+0.2} 1.8±0.1 1.5 ^{+0.2} | By itself the MPT3 has a Pc of 0.5 W (Ta = 25° C), but when used on a $40 \times 40 \times 0.7$ mm ceramic board, Pc = 25° C), allowing high power to be obtained with a small package. The flat package makes it suitable for applications requiring compactness such as hybrid ICs. Available on tape for automatic mounting. |



Packages

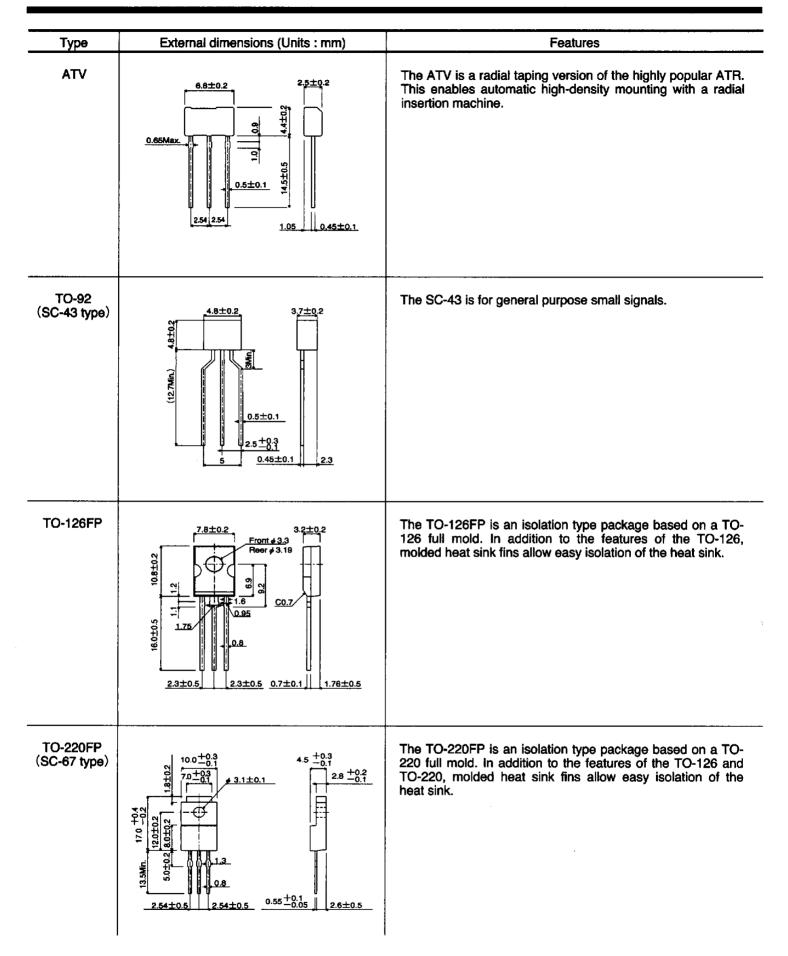
| Туре | External dimensions (Units : mm) | Features |
|---------------------|---|--|
| UMT5 SC-88A type | 2.0±0.2 1.3±0.1 0.65 0.85 0.7 0.7 0.2+0.1 0.2+0.1 0.2+0.1 0.15±0.05 All terminals have same dimensions | The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost. |
| UMT6 SC-88 type | 2.0±0.2 1,3±0.1 0.65 0.7 0.7 0.001 0.2±0.1 0.2±0.1 0.2±0.1 0.15±0.05 All terminals have same dimensions | The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit. |

●Types and features of leaded packages

| Туре | External dimensions (Units : mm) | Features |
|---------------------|---|---|
| SPT (SC-72 type) | 2±0.2 2±0.2 0.45±0.15 0.45±0.05 0.45±0.05 0.45±0.05 0.45±0.05 | The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92. |
| FTR | 0.65±0.1 0.65±0.1 0.65±0.1 0.45±0.1 0.45±0.1 | SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm. |
| FTL | 0.65Max. 0.65Max. 0.5±0.1 0.5±0.1 0.45±0.1 | The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine. |
| ATR (SC-71 type) | 0.65Max. 0.65Max. 0.655 0.4 0.55±0.1 0.55±0.1 | SC-71type with a height of 4.4 mm and a Pc=1W type. |

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Transistors Packages



| Type | External dimensions (Units : mm) | Features |
|----------|--|--|
| TO-220FN | 10.0 ±0.3 4.5 ±0.3 2.8 ±0.2 2.8 ± | The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP. |